# BLC8G21LS-160AV

Power LDMOS transistor

Rev. 4 — 24 May 2017

# 1. Product profile

## 1.1 General description

160 W LDMOS transistor for base station applications at frequencies from 1805 MHz to 2025 MHz.

### Table 1. Typical performance

Typical RF performance at  $T_{case}$  = 25 °C in a Doherty demo board.

Test signal	f	l <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	350	28	22	16	49	-30 [1]
1-carrier W-CDMA	1880 to 2025	350	28	22	15.5	47	-30 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

## **1.2 Features and benefits**

- Designed for broadband operation (1805 MHz to 2025 MHz)
- Decoupling leads to enable improved video bandwidth
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Internally matched for ease of use
- High power gain
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

## **1.3 Applications**

 RF power amplifiers for base station and multi-carrier applications in the 1805 MHz to 2025 MHz frequency range

# 2. Pinning information

Pin	Description	Simplified outli	ne Graphic symbol
1	drain1 (main)		
2	drain2 (peak)		6 1, 5
3	gate1 (main)		
4	gate2 (peak)		7
5	video decoupling (main)		
6	video decoupling (peak)	3 4	2,6
7	source	[1]	aaa-007731

[1] Connected to flange.

# 3. Ordering information

#### Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
BLC8G21LS-160AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1				

# 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

# 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-case)</sub>	thermal resistance from junction to case	T <sub>case</sub> = 80 °C; V <sub>DS</sub> = 28 V; I <sub>Dq</sub> = 400 mA		
		P <sub>L</sub> = 23 W	0.371	K/W
		P <sub>L</sub> = 89 W	0.278	K/W

# 6. Characteristics

#### Table 6.DC characteristics

 $T_i = 25 \ \mathcal{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	vice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 0.72 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 72 mA	1.5	1.9	2.3	V
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 432 mA	1.6	2.1	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	14	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 72 mA	-	0.60	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 2.52 A$	-	205	323	mΩ
Peak dev	vice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 1.1 mA	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 110 mA	1.5	1.9	2.3	V
V <sub>GSq</sub>	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 660 mA	1.6	2.0	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	1.4	μA
I <sub>DSX</sub>	drain cut-off current	V <sub>GS</sub> = V <sub>GS(th)</sub> + 3.75 V; V <sub>DS</sub> = 10 V	-	20	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 110 mA	-	0.97	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 3.85 A$	-	145	215	mΩ

#### Table 7.RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH;  $f_1$  = 1880 MHz;  $f_2$  = 2025 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 200 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 1880 MHz to 2025 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G <sub>p</sub>	power gain	P <sub>L(AV)</sub> = 22.5 W	13.8	15	-	dB
RL <sub>in</sub>	input return loss	P <sub>L(AV)</sub> = 22.5 W	-	-10	-6	dB
$\eta_D$	drain efficiency	P <sub>L(AV)</sub> = 22.5 W	40	45	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 22.5 W	-	-30	-25	dBc

#### Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH; f = 2025 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 200 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 1880 MHz to 2025 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	P <sub>L(AV)</sub> = 60 W	4.3	4.9	-	dB
P <sub>L(M)</sub>	peak output power		158	185	-	W

# 7. Test information

## 7.1 Ruggedness in Doherty operation

The BLC8G21LS-160AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 28 V;  $I_{Dg}$  = 200 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $P_L$  = 120 W (CW); f = 1880 MHz.

## 7.2 Impedance information

#### Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dg}$  = 450 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum p	Maximum power load									
1805	1.63 – j7.04	2.69 – j7.69	87.05	55.92	16.44					
1880	2.43 – j7.93	2.69– j7.69	84.00	55.41	16.40					
1920	3.64 – j9.19	3.32 – j8.33	82.41	58.81	17.29					
2025	9.22 – j10.74	2.69 – j7.69	83.16	60.51	17.28					
Maximum o	drain efficiency load	k	<u>.</u>	i						
1805	1.63 – j7.04	7.07– j5.17	55.89	69.34	19.16					
1880	2.43 – j7.93	5.49 – j4.59	55.05	68.21	19.14					
1920	3.64 – j9.19	4.63 – j4.53	54.27	67.40	18.94					
2025	9.22 – j10.74	3.29 – j5.36	55.68	65.66	18.96					

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] at 3 dB gain compression.

### Table 10. Typical impedance of peak device

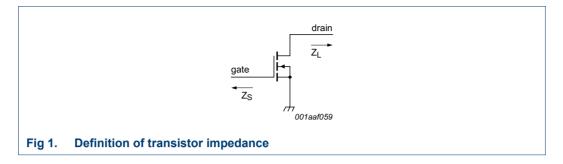
Measured load-pull data of peak device;  $I_{Dg}$  = 600 mA (peak);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum p	laximum power load									
1805	1.11 – j6.63	3.23 – j7.06	126.00	56.38	16.26					
1880	1.60 – j7.94	3.23 – j7.06	122.98	55.66	16.28					
1920	3.45 – j8.58	3.23 – j7.06	120.56	55.34	16.18					
2025	5.33 – j7.56	3.97 – j7.59	128.56	58.56	16.97					
Maximum d	Irain efficiency loa	d								
1805	1.11 – j6.63	5.83 – j3.19	80.08	66.92	18.77					
1880	1.60 – j7.94	4.65 – j3.75	84.85	65.61	18.59					
1920	3.45 – j8.58	3.94 – j3.76	81.80	64.85	18.37					
2025	5.33 – j7.56	3.24 – j4.34	82.20	65.52	18.89					

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] at 3 dB gain compression.

# BLC8G21LS-160AV



## 7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 loadMeasured load-pull data of main device;  $I_{Dq}$  = 450 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	PL <sup>[2]</sup>	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	1.63 – j7.04	4.46 – j6.76	48.9	40.0	21.0
1880	2.43 – j7.93	4.46 – j6.76	48.6	41.0	21.3
1920	3.64 – j9.19	4.46 – j6.76	48.6	41.0	21.3
2025	9.22 - j10.74	3.23 - j7.06	48.7	41.0	21.1

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] at 3 dB gain compression.

[3] at P<sub>L(AV)</sub> = 43.5 dBm.

### Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device;  $I_{Dq}$  = 450 mA (main);  $V_{DS}$  = 28 V.

f	Z <sub>S</sub> <sup>[1]</sup>	Z <sub>L</sub> <sup>[1]</sup>	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	1.63 – j7.04	7.87 – j2.50	46.2	49.5	22.2
1880	2.43 – j7.93	7.43 – j2.21	45.8	53.1	22.9
1920	3.64 – j9.19	7.43 – j2.21	45.8	53.1	22.9
2025	9.22 – j10.74	3.94 – j3.76	45.9	54.6	22.9

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] at 3 dB gain compression.

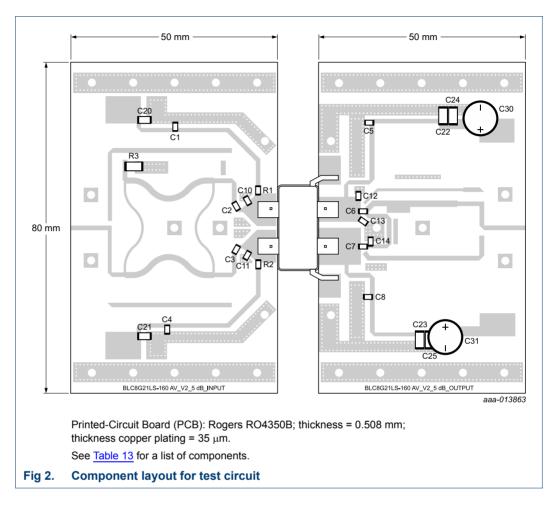
[3] at P<sub>L(AV)</sub> = 43.5 dBm.

## 7.4 VBW in Doherty operation

The BLC8G21LS-160AV shows 110 MHz (typical) video bandwidth in Doherty demo board in 1880 MHz at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 200 mA and  $V_{GS(amp)peak}$  = 0.5 V.

**Power LDMOS transistor** 

## 7.5 Test circuit



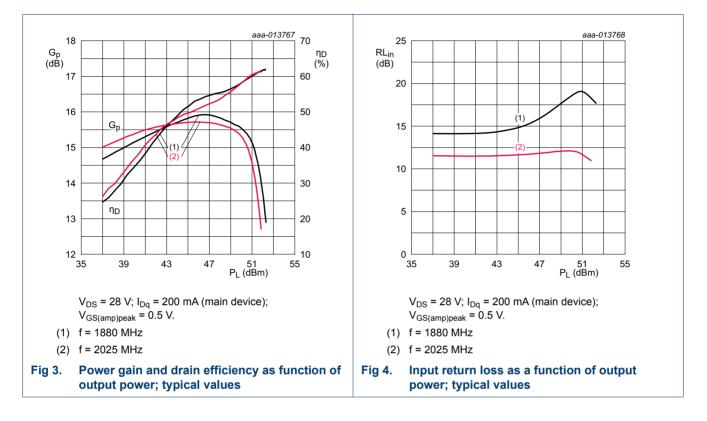
# Table 13.List of componentsSee Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C2, C3, C4, C5, C6, C7, C8	multilayer ceramic chip capacitor	22 pF	
C10	multilayer ceramic chip capacitor	0.3 pF	
C11	multilayer ceramic chip capacitor	0.8 pF	
C12	multilayer ceramic chip capacitor	0.5 pF	
C13	multilayer ceramic chip capacitor	0.7 pF	
C14	multilayer ceramic chip capacitor	1.1 pF	
C20, C21, C22, C23	multilayer ceramic chip capacitor	1 μF, 50 V	
C24, C25	multilayer ceramic chip capacitor	10 μF, 50 V	
C30, C31	electrolytic capacitor	2200 μF, 50 V	
R1, R2	SMD resistor	5.1 Ω	
R3	wire resistor	50 Ω	

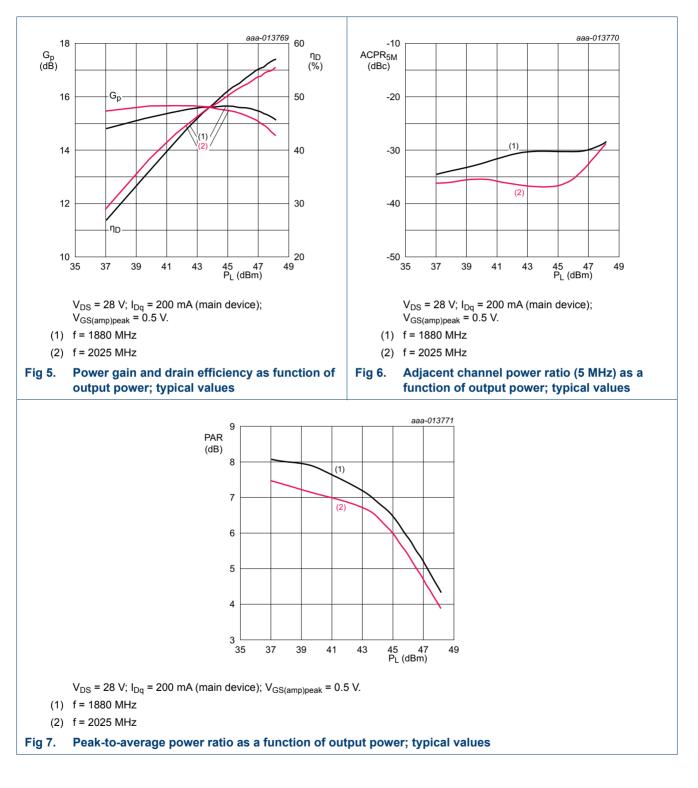
BLC8G21LS-160AV

## 7.6 Graphical data

### 7.6.1 Pulsed CW



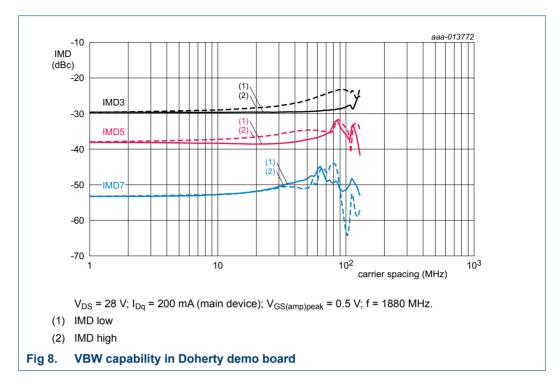
**Power LDMOS transistor** 



### 7.6.2 1-Carrier W-CDMA

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### 7.6.3 2-Tone VBW

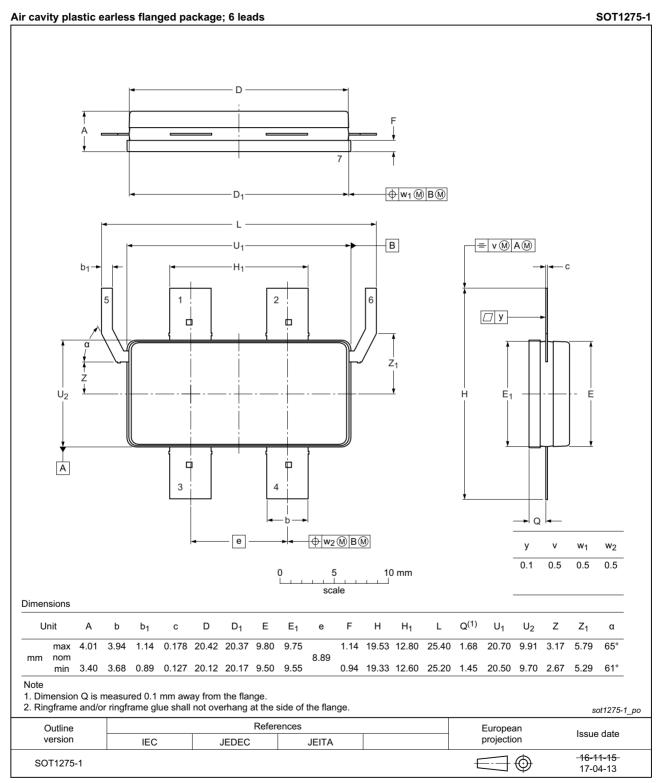


# AMPLEON

BLC8G21LS-160AV

**Power LDMOS transistor** 

# 8. Package outline



### Fig 9. Package outline SOT1275-1

BLC8G21LS-160AV

# 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

#### Table 14.ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

 CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

[2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

# **10. Abbreviations**

#### Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

# 11. Revision history

#### Table 16.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G21LS-160AV v.4	20170524	Product data sheet	-	BLC8G21LS-160AV v.3
Modifications:         • Figure 9 on page 10: updated package outline drawing SOT1275-1				
BLC8G21LS-160AV v.3	20161201	Product data sheet	-	BLC8G21LS-160AV#2
BLC8G21LS-160AV#2	20150901	Product data sheet	-	BLC8G21LS-160AV v.1
BLC8G21LS-160AV v.1	20140812	Product data sheet	-	-

# 12. Legal information

## **12.1 Data sheet status**

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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